

ON THE THEORY OF THE DRAG EFFECT  
UPON NONLINEAR LIGHT ABSORPTION  
IN SEMICONDUCTORS WITH COMPLICATED  
VALENCE BAND

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S u m m a r y

The photon drag effect (PDE) of current carriers upon a nonlinear absorption of polarized light in semiconductors with a complex band structure consisting of two closely located or two degenerate branches has been studied theoretically. The components of the drag current, provided two-photon light absorption, have been analyzed phenomenologically. A contribution of the Rabi effect for one-photon optical transitions, caused by the saturation of the final states of photoexcited holes, to the drag current has been taken into account in quantum-mechanical calculations. Theoretical results are compared with experimental data concerning the PDE in *p*-Ge.